

isc Silicon NPN Pow Transistor

2SC2383

DESCRIPTION

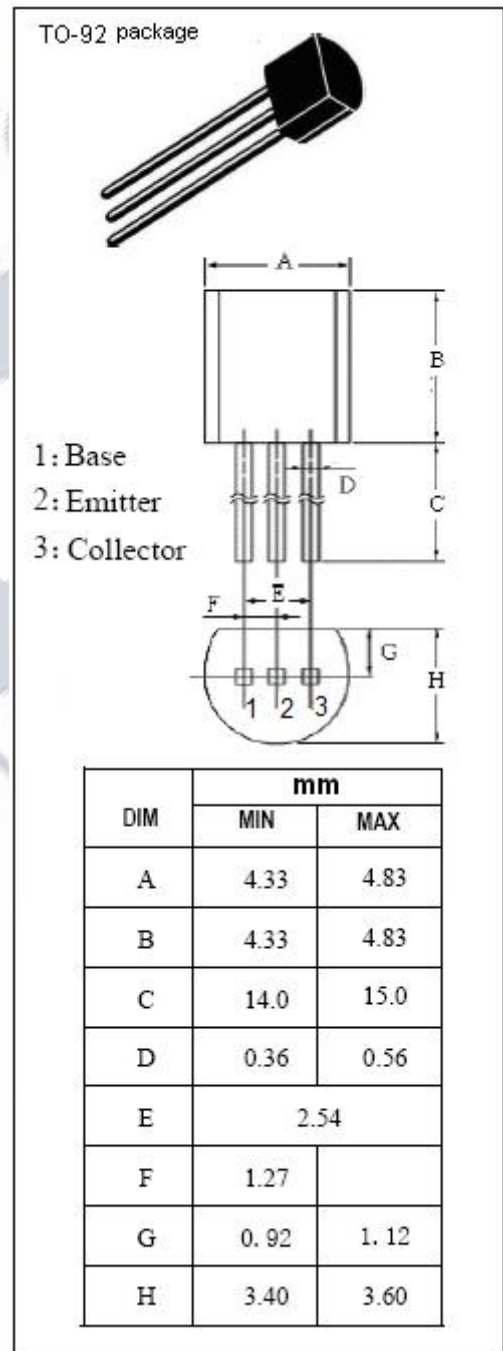
- High breakdown voltage
- Low output capacitance
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Color TV class B sound output applications
- Color TV vert.deflection output applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	160	V
V_{CEO}	Collector-Emitter Voltage	160	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	1	A
I_E	Emitter Current-Continuous	-1	A
P_C	Collector Power Dissipation @ $T_c=25^{\circ}\text{C}$	0.9	W
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}\text{C}$



isc Silicon NPN Pow Transistor**2SC2383****ELECTRICAL CHARACTERISTICS****T_c=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 500mA ; I _B = 50mA			1.5	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = 5mA ; V _{CE} = 5V	0.45		0.75	V
I _{CB0}	Collector Cutoff Current	V _{CB} = 160V; I _E = 0			10	μ A
h _{FE}	DC Current Gain	I _C = 200mA ; V _{CE} = 5V	60		320	
f _T	Current-Gain—Bandwidth Product	I _C = 200mA ; V _{CE} = 5V		20		MHz